### VERY LOW DROP VOLTAGE REGULATOR

 OPERATING DC SUPPLY VOLTAGE RANGE 6V TO 28V

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- TRANSIENT SUPPLY VOLTAGE UP TO 40V
- EXTREMELY LOW QUIESCENT CURRENT
- HIGH PRECISION OUTPUT VOLTAGE
- OUTPUT CURRENT CAPABILITY UP TO 500mA
- VERY LOW DROPOUT VOLTAGE LESS THAN 0.6V
- RESET CIRCUIT SENSING THE OUTPUT VOLTAGE
- PROGRAMMABLE RESET PULSE DELAY WITH EXTERNAL CAPACITOR
- THERMAL SHUTDOWN AND SHORT CIR-CUIT PROTECTIONS

#### DESCRIPTION

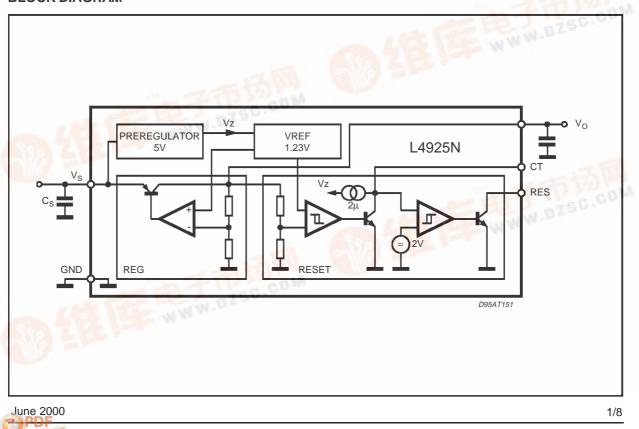
The L4925 is a monolithic integrated 5V voltage regulator with a very low dropout output and addi-

#### **BLOCK DIAGRAM**

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tional functions such as power-on reset and programmable reset delay time. It is designed for supplying microcomputer controlled systems especially in automotive applications.



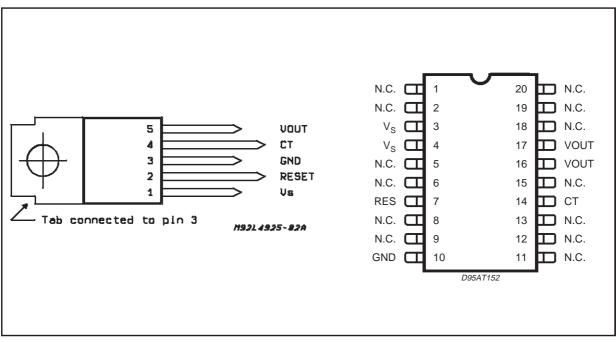
#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>SDC</sub>	DC Operating Supply Voltage	28	V
V <sub>STR</sub>	Transient Supply Voltage (t < 1s)	40	V
lo	Output Current	internally limited	
Vo	Output Voltage	20	V
V <sub>RES</sub>	Output Voltage	20	V
I <sub>RES</sub>	Output Current	5	mA
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C
Tj	Operating Junction Temperature	-40 to 150	°C
T <sub>j-SD</sub>	Thermal Shutdown-Junction Temperature	165	°C

NOTE:

The circuit is ESD protected according to MIL-STD-883C. According to ISO/DIS 7637 the transients must be clamped with external circuitry (see Application Circuit).

#### **CONNECTION DIAGRAM**



#### THERMAL DATA

Symbol	Parameter	Pentawatt	SO 20	Unit
R <sub>th j-amb</sub>	Thermal resistance junction to ambient max.	60	77 to 97	°C/W
R <sub>th j-case</sub>	Thermal resistance junction to case max.	3.5		°C/W

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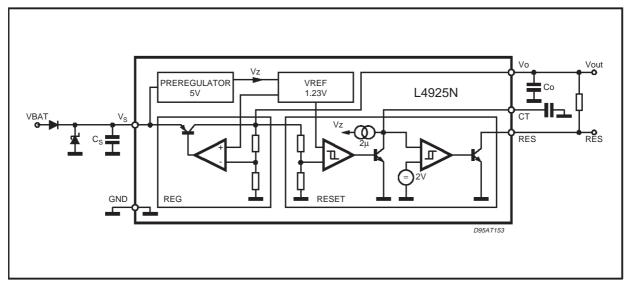
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Vo	Output Voltage	$V_{I} = 6 \text{ to } 28 \text{V}; I_{O} = 1 \text{ to } 500 \text{mA}$	4.90	5	5.10	V
Vo	Output Voltage	V <sub>I</sub> = 35V; T <1s; I <sub>O</sub> = 1 to 500mA			5.50	V
V <sub>DP</sub>	Dropout Voltage	$I_{O} = 100 \text{mA}$ $I_{O} = 500 \text{mA}$		0.2 0.3	0.3 0.6	V V
V <sub>IO</sub>	Input to Output Voltage Difference in Undervoltage Condition	$V_{I} = 4V; I_{O} = 100mA$			0.5	V
Vol	Line Regulation	$V_1 = 6 \text{ to } 28V; I_0 = 1 \text{ to } 1\text{mA}$			10	mV
V <sub>OLO</sub>	Load Regulation	I <sub>O</sub> = 1 to 500mA			50	mV
I <sub>LIM</sub>	Current Limit	$V_0 = 4.5V_{;}$ $V_0 = 0;$ Foldback characteristic	550	1000 250	1500	mA mA
I <sub>QSE</sub>	Quiescent Current	$I_{O} = 0.3 \text{mA}$		190	360	μA
Ι <sub>Q</sub>	Quiescent Current	I <sub>O</sub> = 500mA			20	mA

#### **ELECTRICAL CHARACTERISTICS** (Vs =14V T<sub>j</sub> =-40 to $125^{\circ}$ C unless otherwise specified;

#### RESET

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
V <sub>RT</sub>	Reset Threshold Voltage		4.5		5.2	V
V <sub>RTH</sub>	Reset Threshold		50	100	200	mV
t <sub>RD</sub>	Reset Pulse Delay	C <sub>T</sub> = 100nF; t <sub>R</sub> ≥ 100µs	60	100	140	ms
t <sub>RR</sub>	Reset Reaction Time	CT = 100nF;		5	30	μs
V <sub>RL</sub>	Reset Output LOW Voltage	$R_{RES} = 10 K\Omega$ to $V_0$ ; $V_S = 3V$			0.4	V
I <sub>RH</sub>	Reset Output HIGH Leakage Current	V <sub>RES</sub> = 5V			1	μA
V <sub>CTth</sub>	Delay Comparator Threshold			2		V
VCTth hy	Delay Comparator Threshold Hysteresis			200		mV

#### **APPLICATION CIRCUIT DIAGRAM**



For stability: Cs  $\geq$  1µF; Co  $\geq$  10µF;ESR < 2.5 $\Omega$  at 10 KHz Recommended for application: Cs =Co = 10µF to 100µF

#### **APPLICATION NOTE**

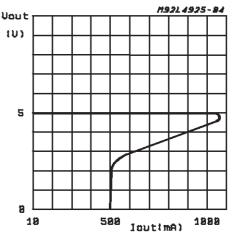
SUPPLY VOLTAGE TRANSIENTS

High supply voltage transients can cause a reset output signal disturbation.

For supply voltage greater than 8V the circuit shows a high immunity of the reset output against supply transients of more than 100V/µs.

For supply voltage lower than 8V, supply transients of more than  $0.4V/\mu s$ . can cause a reset signal disturbation.





#### **FUNCTIONAL DESCRIPTION**

The L4925 is a monolithic integrated voltage regulator, based on the STM modular voltage regulator approach. Several outstanding features and auxiliary functions are implemented to meet the requirements of supplying microprocessor systems in automotive applications.

Nevetrheless, it is suitable also in other applications where the present functions are required. The modular approach of this device allows to get easily also other features and functions when required.

#### **VOLTAGE REGULATOR**

The voltage regulator uses an Isolated Collector Vertical PNP transistor as a regulating element. With this structure very low dropout voltage at currents up to 500mA is obtained.

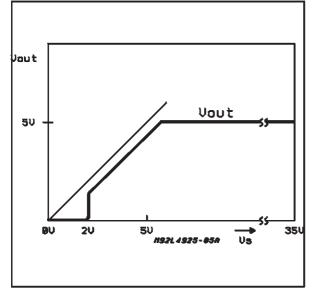


Figure 1: Output Voltage vs. Input Voltage

The dropout operation of the standby regulator is maintained down to 3V input supply voltage. The output voltage is regulated up to the transient input supply voltage of 35V. With this feature no functional interruption due to overvoltage pulses is generated.

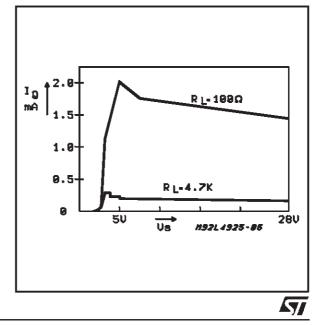
The typical curve showing the standby output voltage as a function of the input supply voltage is shown in fig. 1.

The current consumption of the device (quiescent current) is less than 250µA.

To reduce the guiescent current peak in the undervoltage region and to improve the transient response in this region, the dropout voltage is controlled.

The guiescent current as a function of the supply input voltage is shown in fig. 2.

Figure 2: Quiescent Current vs. Supply Voltage



#### **RESET CIRCUIT**

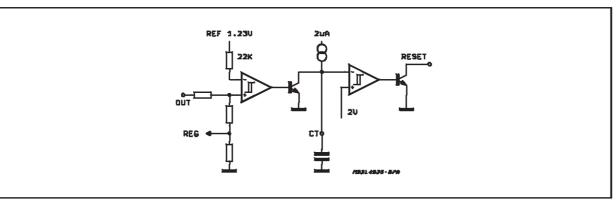
The block circuit diagram of the reset circuit is shown in Figure 3. The reset circuit supervises the output voltage. The reset threshold of 4.5V is defined with the internal reference voltage and standby output divider.

The reset pulse delay time  $t_{RD}$ , is defined with the charge time of an external capacitor  $C_T$ :

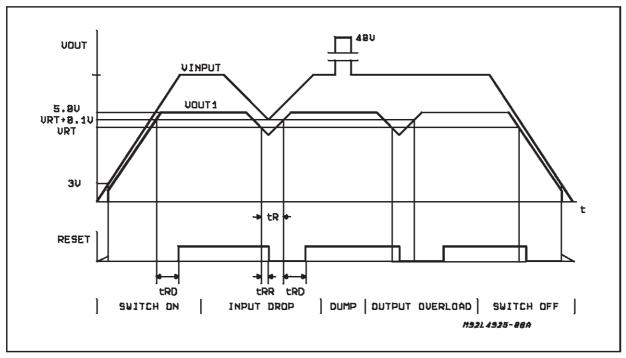
$$t_{RD} = \frac{C_T \times 2V}{2\mu A}$$

The reaction time of the reset circuit originates from the discharge time limitation of the reset capacitor  $C_T$  and it is proportional to the value of  $C_T$ . The reaction time of the reset circuit increases the noise immunity.Standby output voltage drops below the reset threshold only a bit longer than the reaction time results in a shorter reset delay time. The nominal reset delay time will be generated for standby output voltage drops longer than approximately 50 $\mu$ s. The typical reset output waveforms are shown in Figure 4.

#### Figure 3

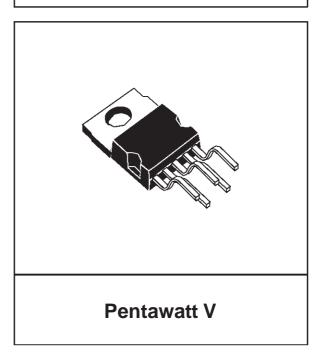


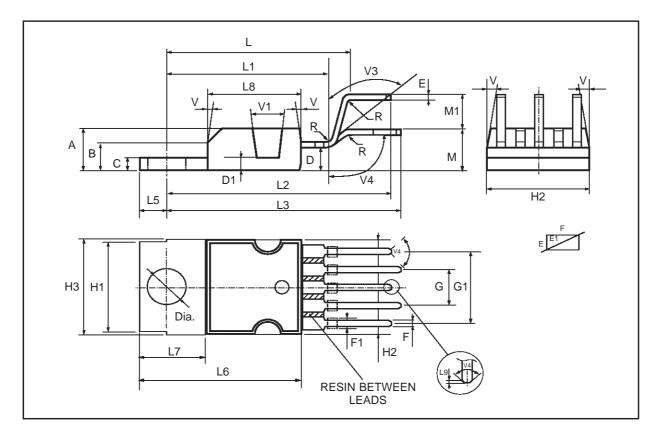
#### Figure 4



DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			4.8			0.189	
С			1.37			0.054	
D	2.4		2.8	0.094		0.110	
D1	1.2		1.35	0.047		0.053	
E	0.35		0.55	0.014		0.022	
E1	0.76		1.19	0.030		0.047	
F	0.8		1.05	0.031		0.041	
F1	1		1.4	0.039		0.055	
G	3.2	3.4	3.6	0.126	0.134	0.142	
G1	6.6	6.8	7	0.260	0.268	0.276	
H2			10.4			0.409	
H3	10.05		10.4	0.396		0.409	
L	17.55	17.85	18.15	0.691	0.703	0.715	
L1	15.55	15.75	15.95	0.612	0.620	0.628	
L2	21.2	21.4	21.6	0.831	0.843	0.850	
L3	22.3	22.5	22.7	0.878	0.886	0.894	
L4			1.29			0.051	
L5	2.6		3	0.102		0.118	
L6	15.1		15.8	0.594		0.622	
L7	6		6.6	0.236		0.260	
L9		0.2			0.008		
М	4.23	4.5	4.75	0.167	0.177	0.187	
M1	3.75	4	4.25	0.148	0.157	0.167	
V4	40°(typ.)						

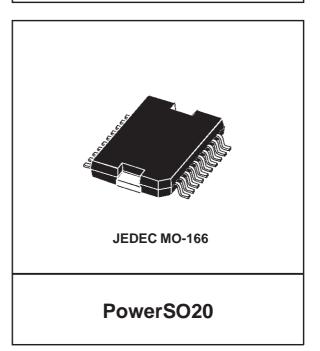
#### OUTLINE AND MECHANICAL DATA



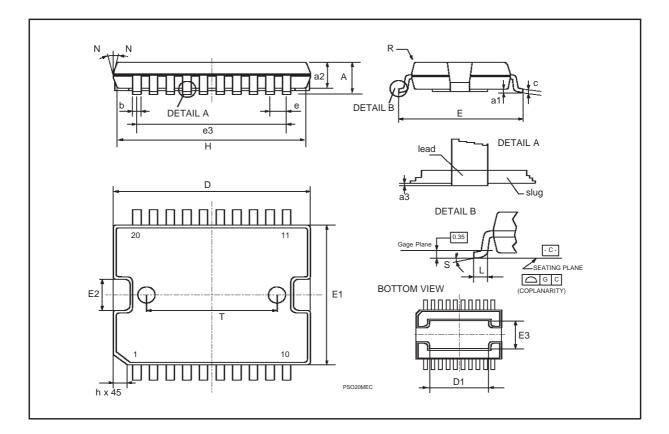


DIM.	mm			inch			
DINI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			3.6			0.142	
a1	0.1		0.3	0.004		0.012	
a2			3.3			0.130	
a3	0		0.1	0.000		0.004	
b	0.4		0.53	0.016		0.021	
с	0.23		0.32	0.009		0.013	
D (1)	15.8		16	0.622		0.630	
D1	9.4		9.8	0.370		0.386	
Е	13.9		14.5	0.547		0.570	
е		1.27			0.050		
e3		11.43			0.450		
E1 (1)	10.9		11.1	0.429		0.437	
E2			2.9			0.114	
E3	5.8		6.2	0.228		0.244	
G	0		0.1	0.000		0.004	
Н	15.5		15.9	0.610		0.626	
h			1.1			0.043	
L	0.8		1.1	0.031		0.043	
Ν	10° (max.)						
S	8° (max.)						
Т		10			0.394		

# OUTLINE AND MECHANICAL DATA



- Mold flash or protrusions shall not exceed 0.15 mm (0.006"). - Critical dimensions: "E", "G" and "a3"



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